

# VES

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Device Type	$V_{RRM}$ (1)	$V_{DRM}$ (1)	$V_{RSM}$ (1)
KP1800/20	2000	2000	2200
KP1800/22	2200	2200	2400
KP1800/24	2400	2400	2500

$V_{RRM}$  = Repetitive peak reverse voltage  
 $V_{DRM}$  = Repetitive peak off state voltage  
 $V_{RSM}$  = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage  $I_{RRM} \hat{A} / E$

KP1800

# gde

Peak gate power dissipation	$P_{GM}$		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	$I_{GT}$		200		mA	$V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^\circ\text{C}$
Gate- trigger voltage	$V_{GT}$	0.7	3.0		V	$V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^\circ\text{C}$
Peak negative voltage	$V_{GRM}$		5		V	

Delay time	$t_d$		3.0	2.5	s	$I_{TM}=100\text{A}; V_D=67\%V_{DRM}$ $V_G=30\text{V}; R_G=10\text{ohms};$ $t_r=0.1\text{ s}; t_p=20\text{ s}$
Turn-off time (with $V_R = -5\text{ V}$ )	$t_q$			350	s	$I_{TM}=2000\text{A}; di/dt=-10\text{A/ s};$ $V_R=100\text{V}; dv/dt=30\text{V/ s};$ $V_D=67\%V_{DRM}; T_j=125$
Reverse recovery charge	$Q_{rr}$				C	$I_{TM}=2000\text{A } di/dt=-10\text{A/ s};$ $V_R=100\text{V}; T_j=125$

Operating temperature	$T_j$	-40	+125	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-40	+140	$^\circ\text{C}$	
Thermal resistance - junction to case	$R_{(j-c)}$		0.015	$^\circ\text{C/W}$	Double sided cooled
Thermal resistance - case to heatsink	$R_{(c-s)}$		0.00-	r	



